

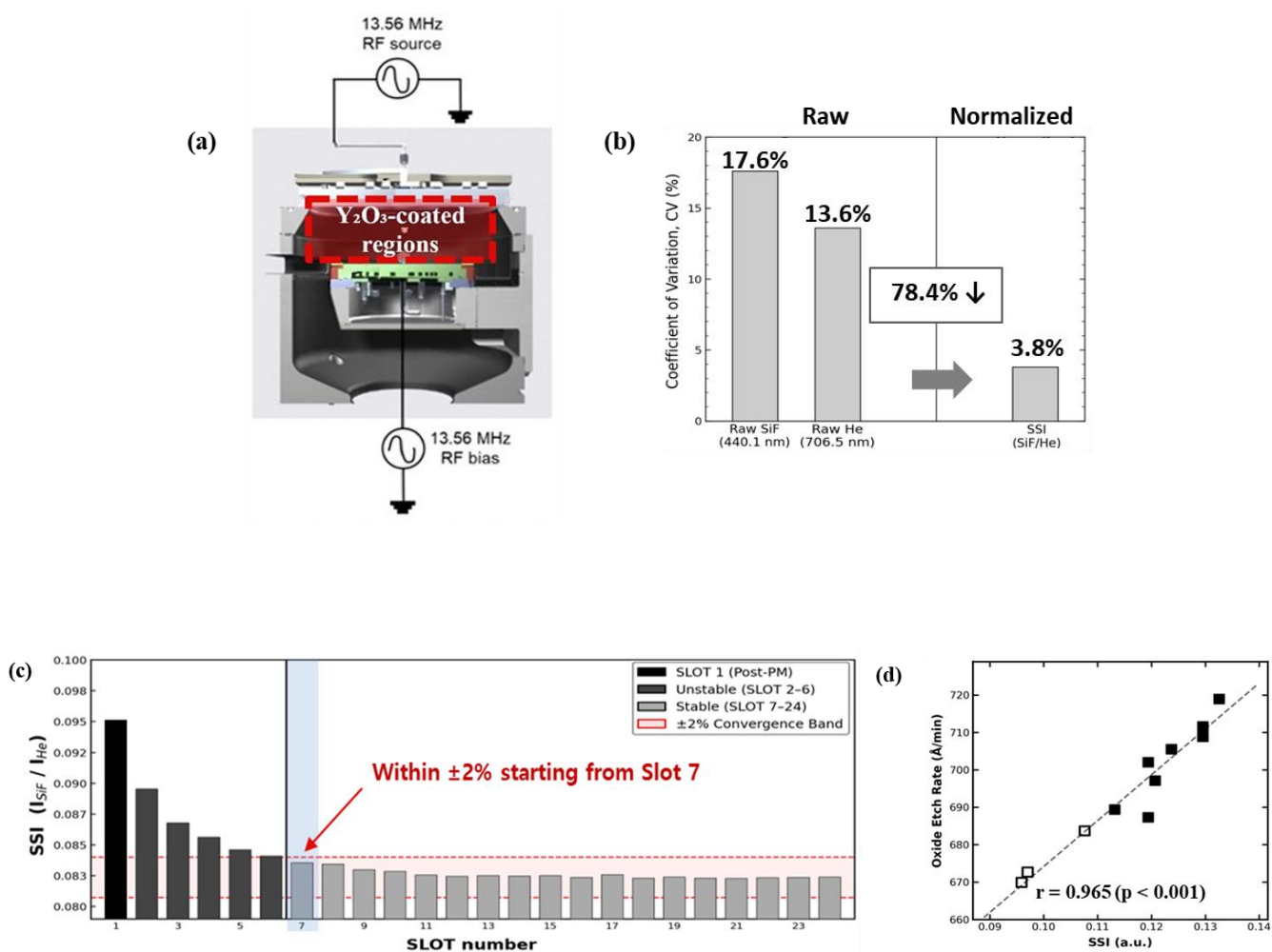


Fig. 1. (a) Schematic of the 300 mm ICP etcher with Y_2O_3 -coated chamber walls / (b) Coefficient of variation of raw SiF, raw He, and He-normalized SSI (SiF/He) / (c) SSI values as a function of conditioning wafer slot number showing convergence to the $\pm 2\%$ stability band at Slot 7. / (d) Correlation between SSI and blanket oxide etch rate ($\text{\AA}/\text{min}$).